



PATENT APPLICATION
Docket No. 2522-040
Client No. AW8072US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Jae-Jong Han, et al. Conf. No. 9537
Serial No. 10/672,884 Examiner: Lee, Hsien Ming
Filed: September 26, 2003 Art Unit: 2823
For: METHOD OF FORMING A GATE ELECTRODE, METHOD OF
MANUFACTURING A SEMICONDUCTOR DEVICE HAVING
THE GATE ELECTRODE, AND METHOD OF OXIDIZING A
SUBSTRATE

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)

FOREIGN PATENT DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Publication</u> <u>Number</u>	<u>Publication</u> <u>Date</u>	<u>Country</u>	<u>Name</u>
<i>Lee</i>	—	000061321 A	Oct. 16, 2000	Korea	EOM, et al.

*CLASS 503
SUB CLASS*

OTHER DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Author, Title, Date, Pertinent Pages, Etc.)</u>
<i>Lee</i>	—	English Language Abstract of Korean Publication No: 000061321 A

Examiner: *Hsien Ming Lee*

Date Considered: *11/8/2004*

paper no: 111704